

White Paper XII

Traditional Science Tiller Publication List

1. The Redistribution of Solute During the Solidification of Metals (with K.A. Jackson, J.W. Rutter and B. Chalmers) Acta Met. 1, p. 428 (1953).
2. Instability of a Smooth Solid – Liquid Interface During Solidification, (with D. Walton, J.W. Rutter and W.C. Winegard) Trans. AIME, 203, 1023 (1955).
3. Conditions for Dendritic Growth in Alloys, (with W. Morris, J.W. Rutter, and W.C. Winegard) ASM Transactions, p. 463 (1955).
4. Grain Boundary Segregation, (with W.C. Winegard) Acta Met. 3, (1955).
5. A Mathematical Analysis of Solute Redistribution During Solidification, (with V.G. Smith and J.W. Rutter) Canadian Journal of Physics, 33, 723 (1955).
6. The Effect of Growth Conditions Upon the Solidification of a Binary Alloy, (with J.W. Rutter) Canadian Journal of Physics, 34, 96 (1956).
7. Growth Twins in Germanium, (with G.F. Bolling and J.W. Rutter) Canadian Journal of Physics, 34, 234 (1956).
8. Alloy Dendritic Growth, Canadian Journal of Physics, 34, 729 (1956).
9. The Modification of Eutectic Structures, Acta Met., 5, 56 (1957).
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13. Solute Segregation During Ingot Solidification, Journal of British Iron and Steel Inst., 192, 338 (1959).
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26. The Application of Ultrasonic Energy to Ingot Solidification – Part I, (with D.H. Lane and J.W. Cunningham) Trans. AIME, 218, 986 (1961).
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28. Crystal Growth: The Science and Engineering of Thermoelectricity by R.R. Heikes and R. Ure (Interscience, 1961), Chapter 8.
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